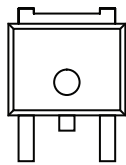


## Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
$V_{DS}$ (V)	60
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10$ V	0.022
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.032
$I_D$ (A)	25
Configuration	Single

**FEATURES**

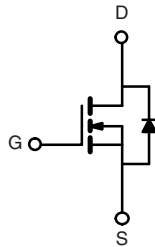
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified<sup>d</sup>
- Compliant to RoHS Directive 2002/95/EC
- Find out more about Vishay's Automotive Grade Product Requirements at: [www.vishay.com/applications](http://www.vishay.com/applications)


**TO-252**


G D S

Top View

Drain Connected to Tab



N-Channel MOSFET

**ORDERING INFORMATION**

Package	TO-252
Lead (Pb)-free and Halogen-free	SQD25N06-22L-GE3

**ABSOLUTE MAXIMUM RATINGS**  $T_C = 25$  °C, unless otherwise noted

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>a</sup>	$I_D$	$T_C = 25$ °C	25
		$T_C = 100$ °C	16
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	25	A
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	30	
Single Pulse Avalanche Energy	$E_{AS}$	31.25	mJ
Single Pulse Avalanche Current			
Maximum Power Dissipation <sup>b</sup>	$P_D$	50	W
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to + 175	°C

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	$R_{thJA}$	60	°C/W
Junction-to-Case (Drain)			

**Notes**

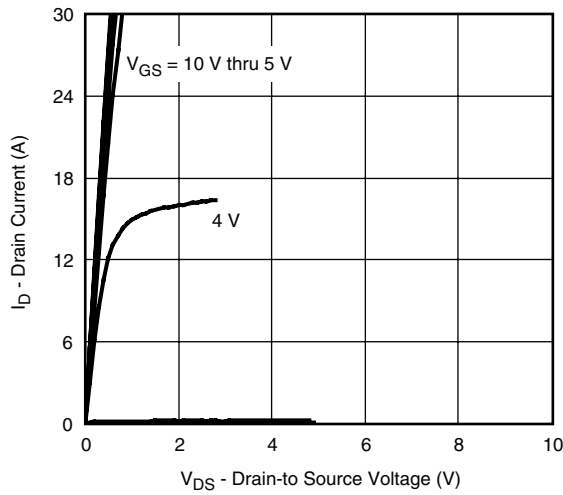
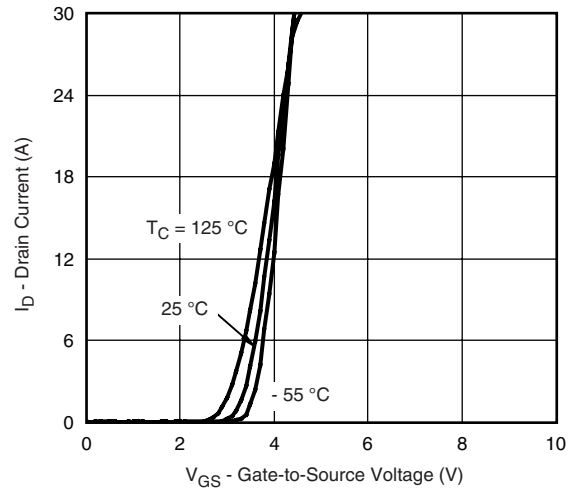
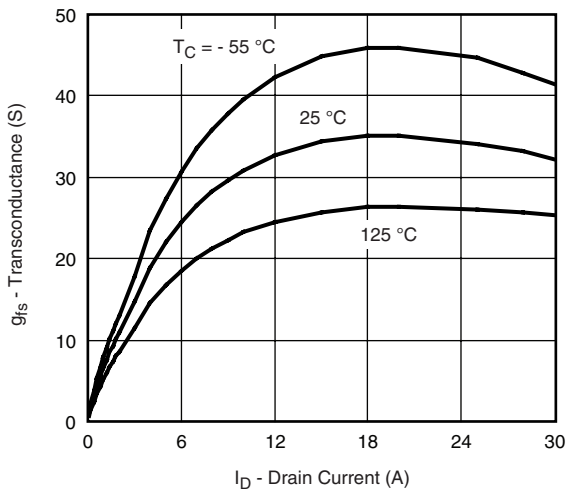
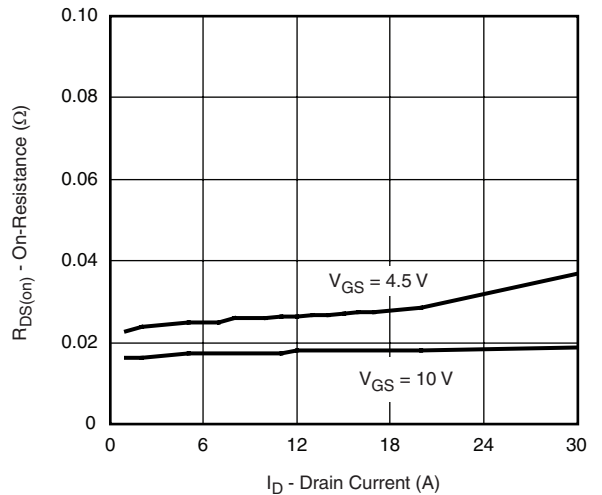
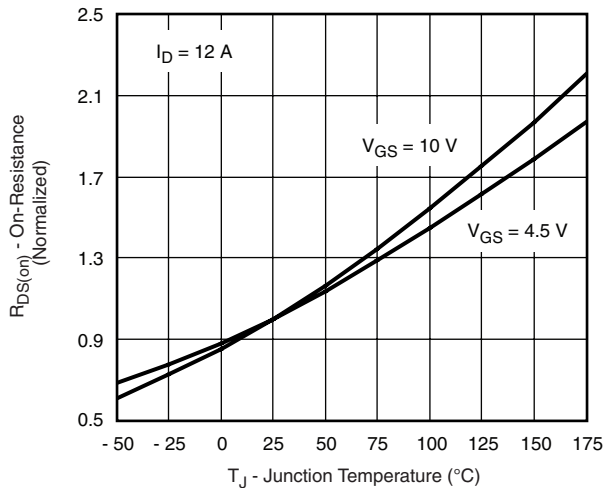
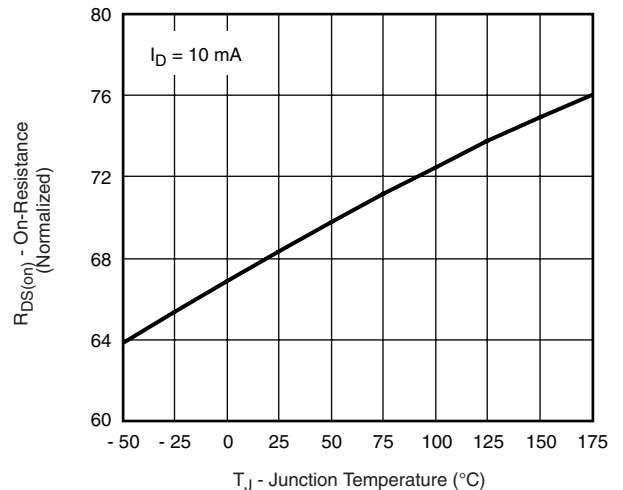
- Package limited.
- Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %.
- When mounted on 1" square PCB (FR-4 material).
- Parametric verification ongoing.

<b>SPECIFICATIONS</b> $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$		60	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$		1.5	2.0	2.5	
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$	-	-	1.0	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 60\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$	-	-	250	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	25	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}$	-	0.018	0.022	$\Omega$
		$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$	-	-	0.036	
		$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}$ , $T_J = 175\text{ }^\circ\text{C}$	-	-	0.043	
		$V_{GS} = 4.5\text{ V}$	$I_D = 20\text{ A}$ , $T_J = 25\text{ }^\circ\text{C}$	-	0.027	0.032	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}$ , $I_D = 12\text{ A}$		-	25	-	S
<b>Dynamic<sup>b</sup></b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$	-	1500	-	$\mu\text{F}$
Output Capacitance	$C_{oss}$			-	320	-	
Reverse Transfer Capacitance	$C_{rss}$			-	65	-	
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{GS} = 10\text{ V}$	$V_{DS} = 30\text{ V}$ , $I_D = 50\text{ A}$	-	30	-	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			-	10	-	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	12	-	
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}$ , $R_L = 1.2\text{ }\Omega$ $I_D \cong 25\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 7.5\text{ }\Omega$		-	10	-	ns
Rise Time <sup>c</sup>	$t_r$			-	10	-	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			-	35	-	
Fall Time <sup>c</sup>	$t_f$			-	12	-	
<b>Source-Drain Diode Ratings and Characteristics</b> $T_C = 25\text{ }^\circ\text{C}$ <sup>b</sup>							
Pulsed Current <sup>a</sup>	$I_{SM}$			-	-	30	A
Forward Voltage	$V_{SD}$	$I_F = 25\text{ A}$ , $V_{GS} = 0\text{ V}$		-	1.0	1.5	V

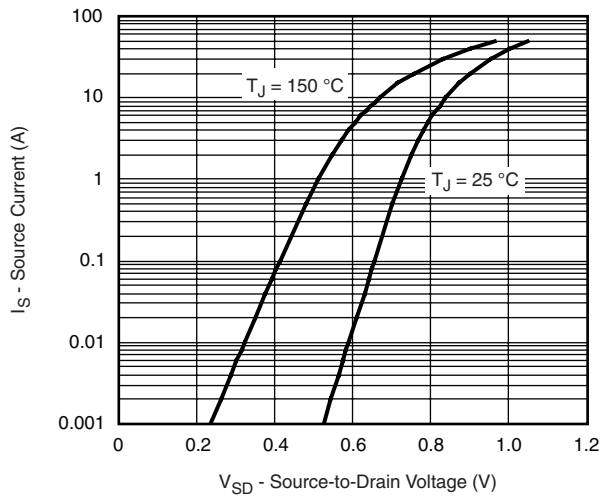
### Notes

- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

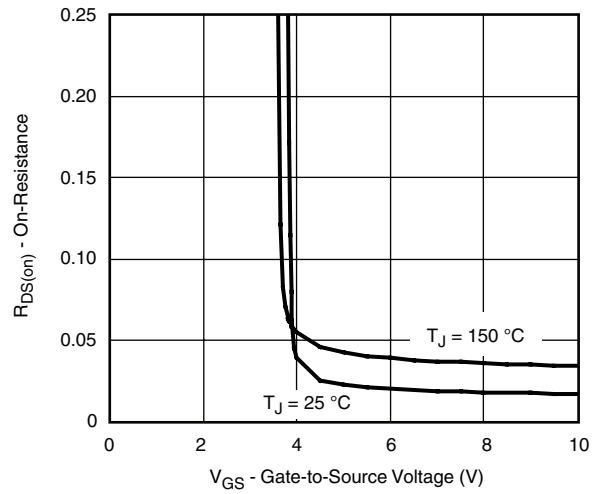
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS**  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted

**Output Characteristics**

**Transfer Characteristics**

**Transconductance**

**On-Resistance vs. Drain Current**

**On-Resistance vs. Junction Temperature**

**On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS**  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted

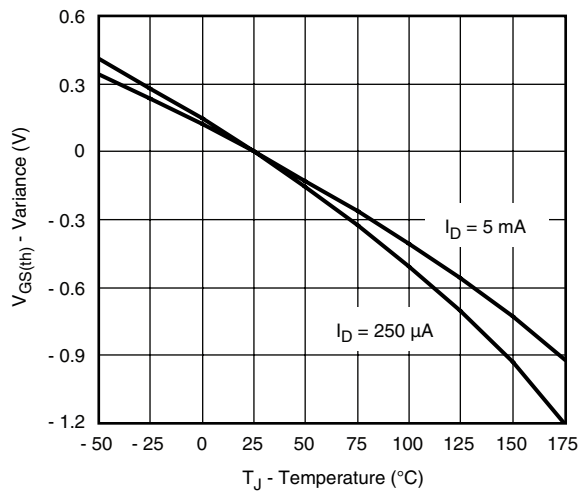


**Source Drain Diode Forward Voltage**



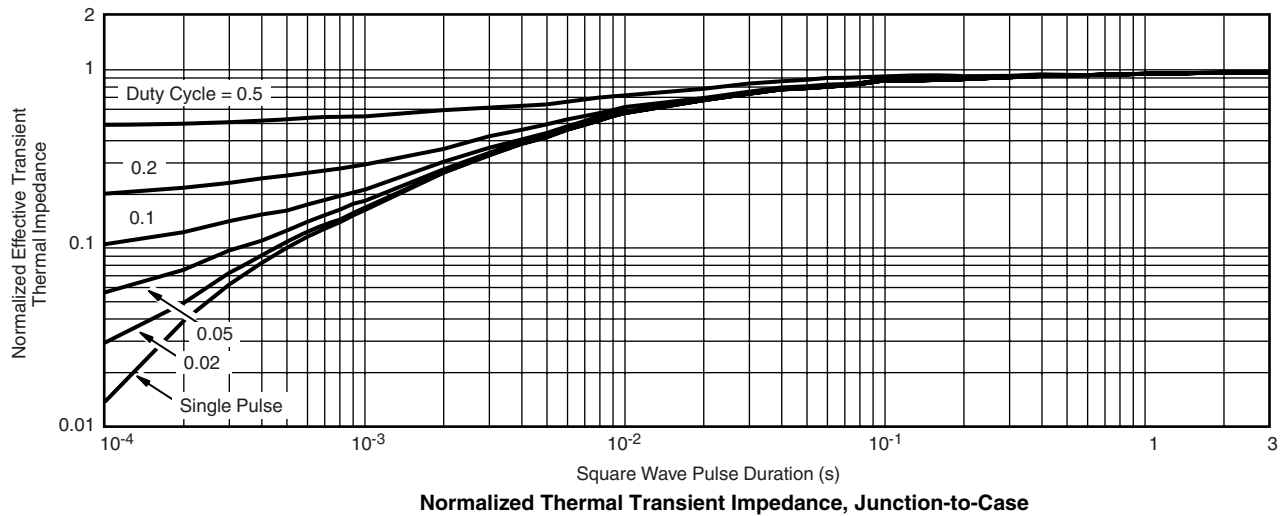
**On-Resistance vs. Gate-to-Source Voltage**

**THERMAL RATINGS**  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted



**Threshold Voltage**

**THERMAL RATINGS**  $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted



**Note**

The characteristics shown in the graph. Normalized Transient Thermal Impedance Junction to Case ( $25\text{ }^\circ\text{C}$ ) is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

*Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?65360](http://www.vishay.com/ppg?65360).*



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